

ERRATA

Source references for the corresponding figures are added to the following figure captions. The correct form of the caption or part of the caption is in quotation marks;

- **Figure 2.1:** "Unit cell of wurtzite GaN [5]."
- **Figure 2.2:** "The epitaxial relationship of wurtzite GaN and c-plane sapphire (modified from Ref. 5)."
- **Figure 2.5:** "The energy bandgap of III-nitride binary compounds vs. their lattice constant a (modified from Ref. 5)."
- **Figure 3.1:** "The measurement setup for *in-situ* reflectometry in the MOCVD system used for this work (modified from Ref. 20)."
- **Figure 3.2:** "Notations used for the derivation of reflectance in a one-film structure [20]."
- **Figure 3.3:** "Operating principle of the AFM apparatus used in this work (modified from Ref. *).", *where the reference, "[*] J. Sormunen, Growth and Modification of Planar and Self-Assembled Semiconductor Nanostructures, dissertation, Helsinki University of Technology, (2006).", is added to the reference list.*
- **Figure 3.4:** "Schematic of the XRD measurement setup. This setup was used to perform the high resolution (HR) XRD scans on the studied III-nitride films (modified from Ref. **).", *where the reference, "[**] L. Knuutila, Growth and Properties of Compound Semiconductors on Germanium Substrate, dissertation, Helsinki University of Technology, (2006).", is added to the reference list.*
- **Figure 4.2:** "Structure of the CCS reaction chamber in the MOCVD system [***].", *where the reference, "[***] Thomas Swan Scientific Equipment Ltd., (2004).", is added to the reference list.*
- **Figure 4.3:** "Diagram illustrating the temperature profile and the timing of precursor flows during the two-step growth of GaN (modified from Ref. 20)."
- **Figure 5.1:** Last line of the figure caption is; "neighboring NIs (modified from Publ. I)."
- **Figure 6.13:** Last line of the figure caption is; "resulting from the multistep (conventional two-step) method (modified from Publ. VI)."